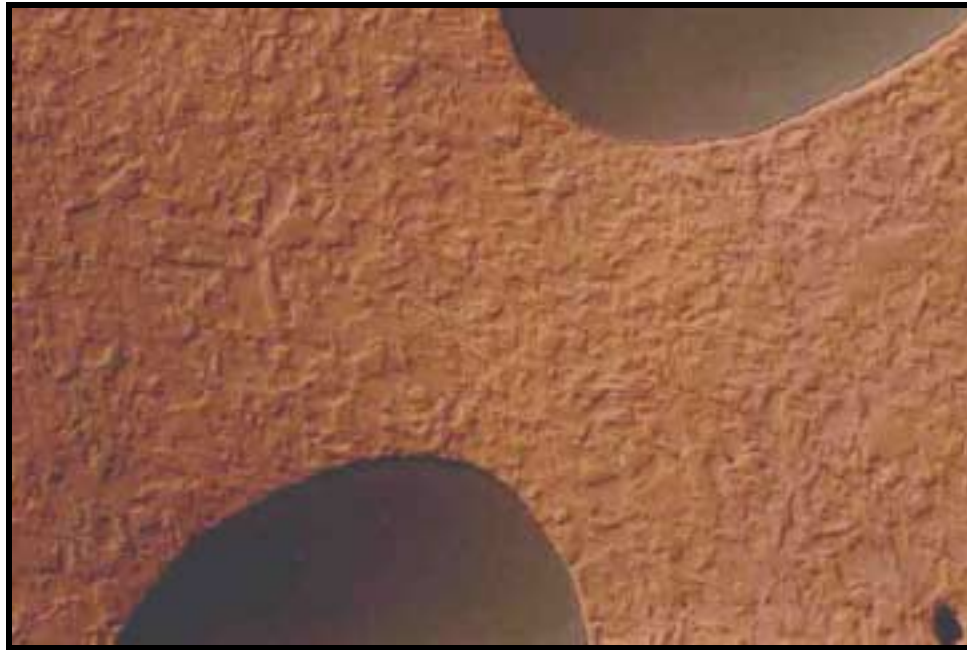


MetPrep Preparation Procedure – No 193



Low Temperature Super Conductor Wire

	Surface	Abrasive	Pressure		Speed – Dir	Time
			Psi	N		
Primary Grinding Stage	Paper	P240g SiC	5	25	150 – Comp	Until Planar

	Surface	Abrasive	Pressure		Speed – Dir	Time
			Psi	N		
Additional Grinding Stages	Planocloth H	9 µm (WB) PCD Diamond	5	25	250 – Comp	5 mins
	Chrysalis	3 µm (WB) PCD Diamond	5	25	250 – Comp	4 mins

	Surface	Abrasive	Pressure		Speed – Dir	Time
			Psi	N		
Polishing Stage	Multicloth	0.06µm Silco	3	15	80 – Comp	2 mins